



The University of
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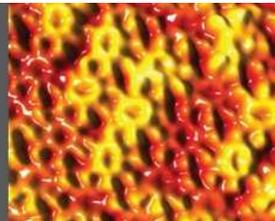
Surface morphology and magnetic anisotropy in (Ga,Mn)As

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**Interdisciplinary Surface
Science Conference (ISSC-19)**

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Spintronics

A new scheme of electronics using the charge and the spin of the electron

Semiconductor devices

- ✓ Transistor
- ✓ LED
- ✓ CPU,...



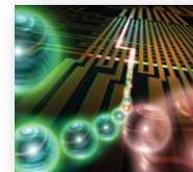
Magnetic devices

- ✓ Non-volatile memory
- ✓ Storage
- ✓ Magneto-optical devices,...



Ferromagnetic semiconductor

- ✓ spin and charge of electrons as information carriers
- ✓ storing and manipulating data
- ✓ faster and smaller memories



Motivations



Applications

- ✓ Realisation of devices for **spintronics** industry and quantum information

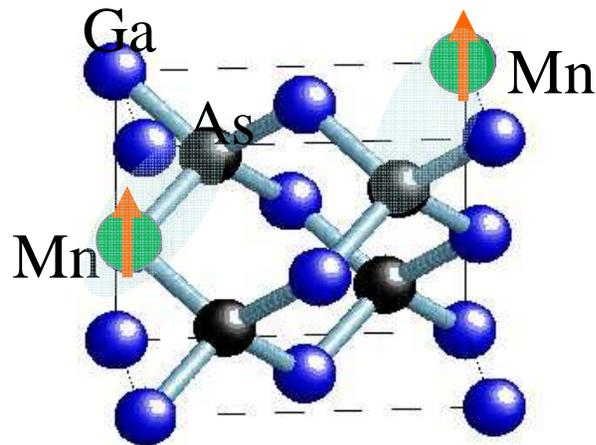
Fundamental physics

- ✓ Study of magnetic properties
- ✓ Understanding the microscopic origin of the **magnetic anisotropy**

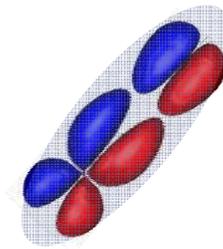
Contents

- ✓ Introduction to (Ga,Mn)As
- ✓ AFM images
- ✓ Study of the ripples with Fourier analysis
- ✓ Relation between ripples and magnetic anisotropy
- ✓ GID experiments and analysis
- ✓ Conclusions and future perspectives

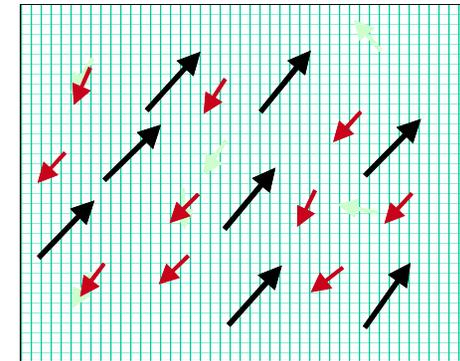
(Ga,Mn)As



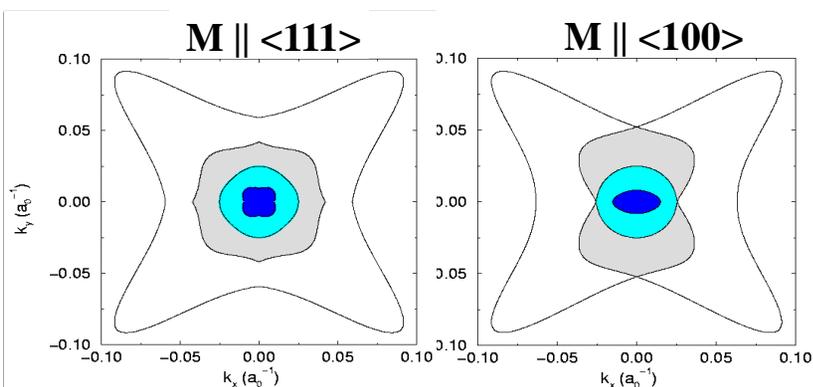
As-p-like holes



Mn-d-like local moments



Ferromagnetic order is mediated by the itinerant holes for few % Mn
Holes possess **strong SO-coupling**



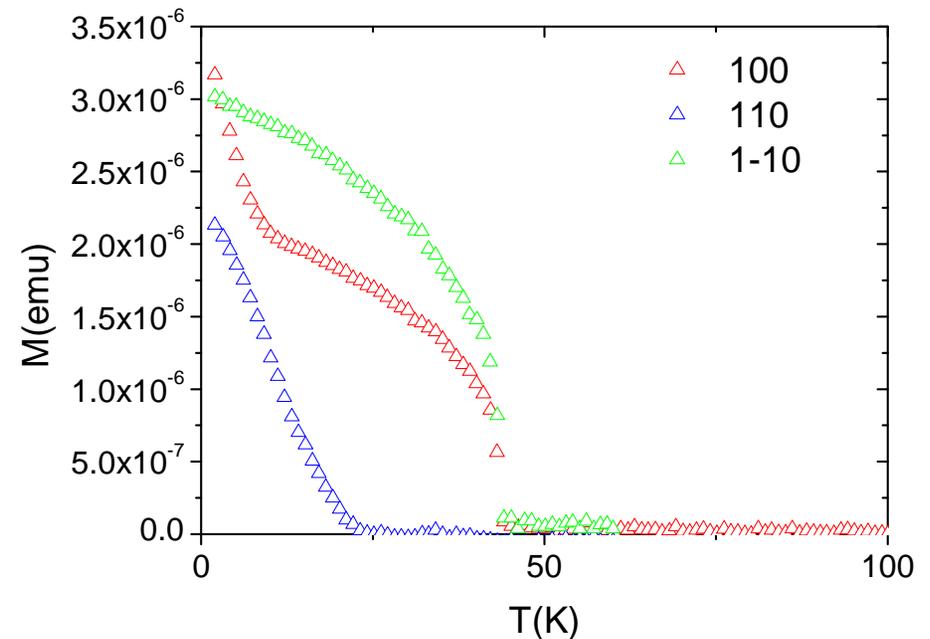
Anisotropy

- ✓ Spin-orbit coupling gives rise to large **magnetocrystalline anisotropy**
- ✓ The anisotropy is sensitive to the lattice strain and the carrier density

Magnetic properties

Remanent measurements

- *dominant in plane [1-10] uniaxial magnetic easy axis at high temperature*
- *competition between in plane [1-10] uniaxial and in-plane [100] bi-axial easy axes at low temperatures.*



Magnetic anisotropy

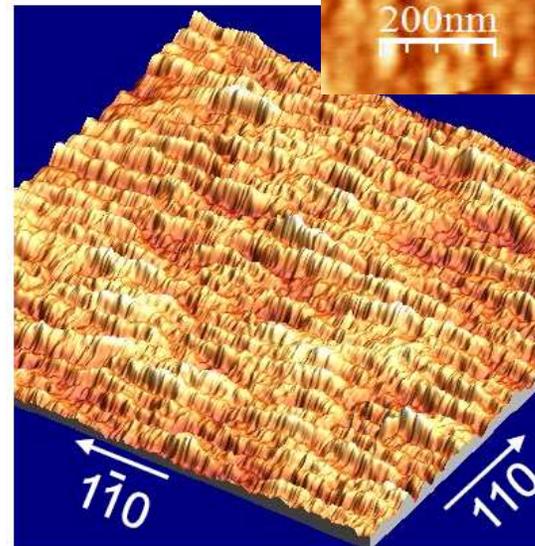
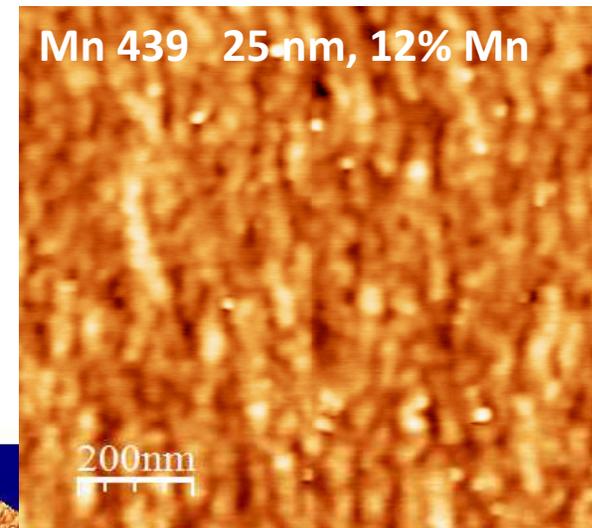
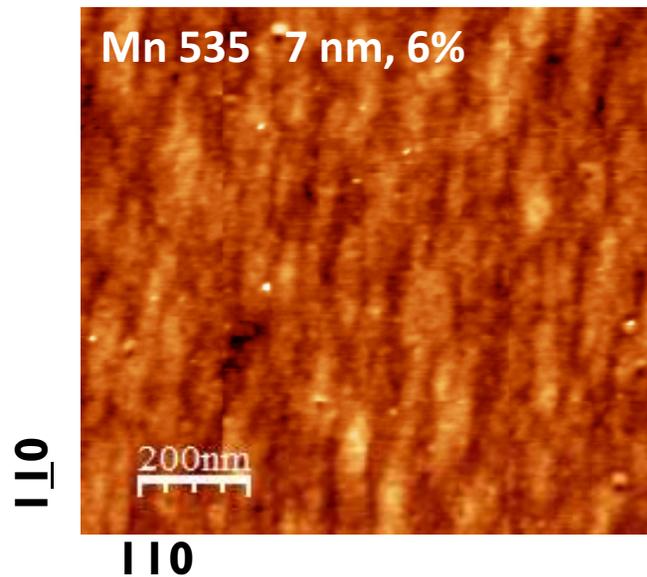
the relative strength of the uniaxial to cubic anisotropy is phenomenologically described by:

$$\frac{K_U}{K_C} = \cos 2\left[\arctan \frac{M_{1\bar{1}0}}{M_{110}}\right]$$

(Ga,Mn)As growth

- ▶ Molecular Beam Epitaxy growth ($\sim 200\text{ }^{\circ}\text{C}$)
 - ▶ GaAs (100 nm) substrates
 - ▶ GaAs or AlGaAs buffer layer
 - ▶ 5, 7 and 25 nm thick
 - ▶ 6% and 12% Mn concentration

Atomic Force Microscopy



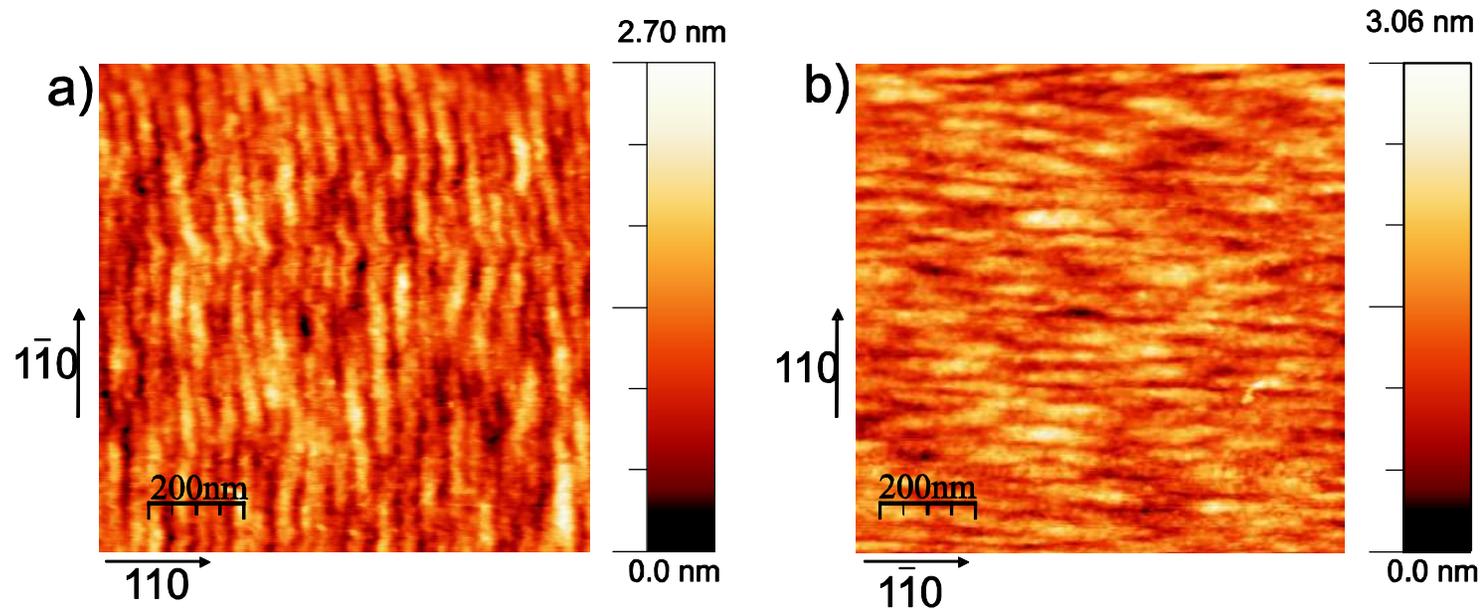
Mn 381 7 nm, 6% Mn

AFM images:

Asylum Research MFP-3D AFM

Presence of ripples along $1\bar{1}0$ direction for all the analysed samples

Atomic Force Microscopy

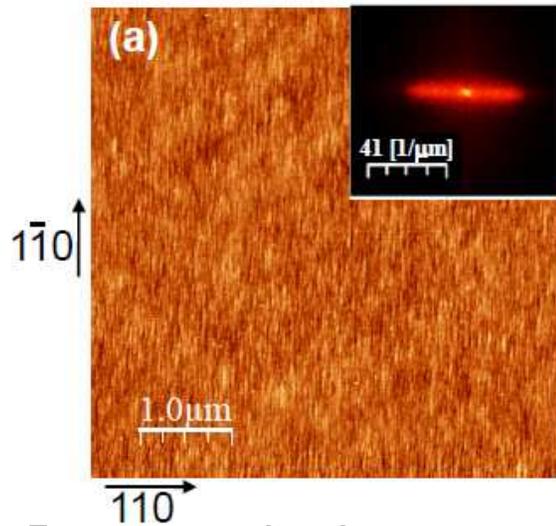


▶ Fourier analysis

to extract quantitative information from these images

- ▶ Effective period of the oscillations
- ▶ Root mean square roughness (RMS)

2D Power Spectral Density



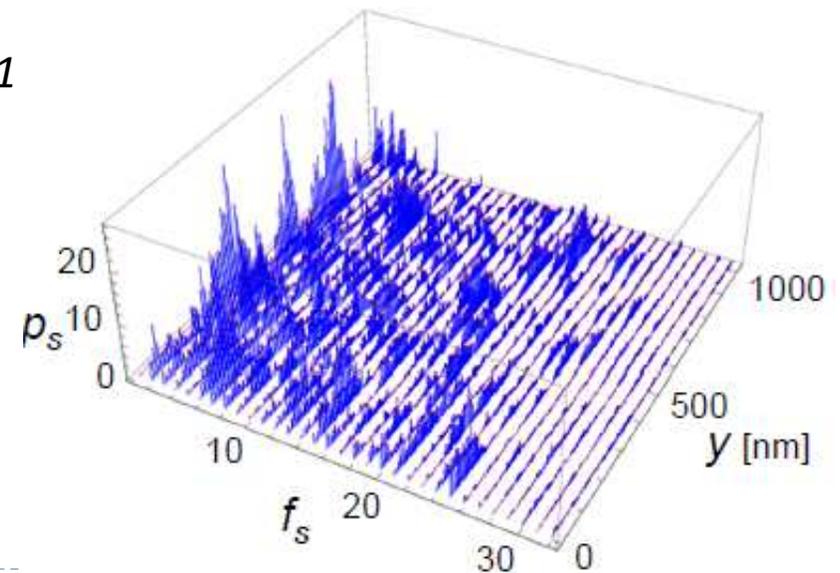
The 2D PSD spectrum shows clearly the **surface anisotropy**, indicating that periodicity across the horizontal direction is strongly enhanced compared to the vertical one

Fourier amplitude corresponding to a frequency $f_s = s-1$

$$\phi_s = \frac{1}{\sqrt{n}} \sum_{r=1}^n z_r e^{2\pi(r-1)(s-1)/n}$$

The PSD is defined as

$$p_s = |\phi_s|^2$$

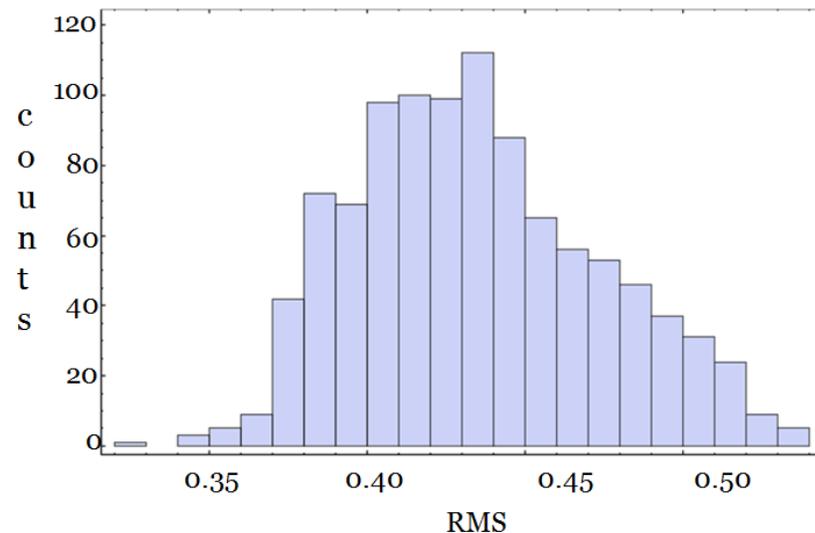


Amplitude

RMS roughness as standard deviation of the $z(y)$ height data and it is equal to the amplitude (A) of the oscillations

$$A = \sqrt{2}RMS = \frac{\sqrt{2\sum_{s=1}^n p_s}}{n-1}$$

Distribution of the RMS across the horizontal scan lines



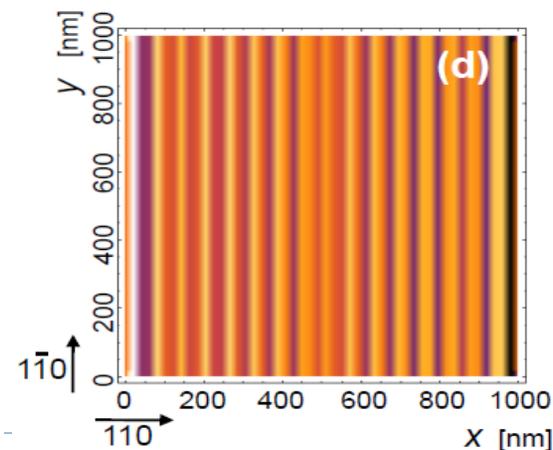
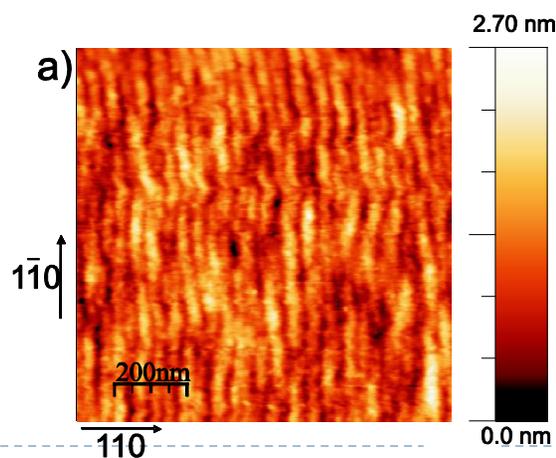
Period

The **mean frequency** per line is an average of the frequencies of all Fourier harmonics (along a given horizontal scan line) weighted with the corresponding PSDs

$$\bar{f}(y) = \frac{\sum_{s=1}^{n/2} (s-1) p_s}{\sum_{s=1}^{n/2} p_s}$$

the global “effective” mean frequency is given by the mean of the $f(y)$'s of each line y along all horizontal scan lines

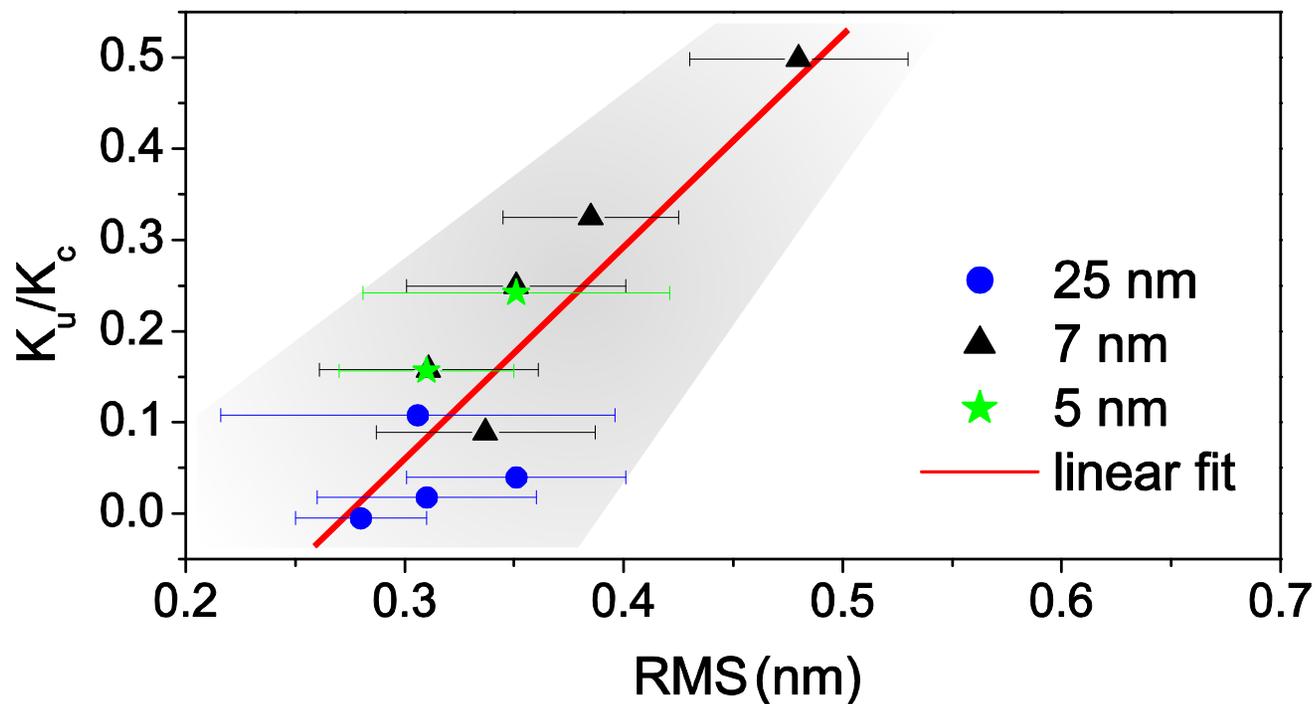
Period of the oscillations: $\tau = \frac{L}{f}$



Data

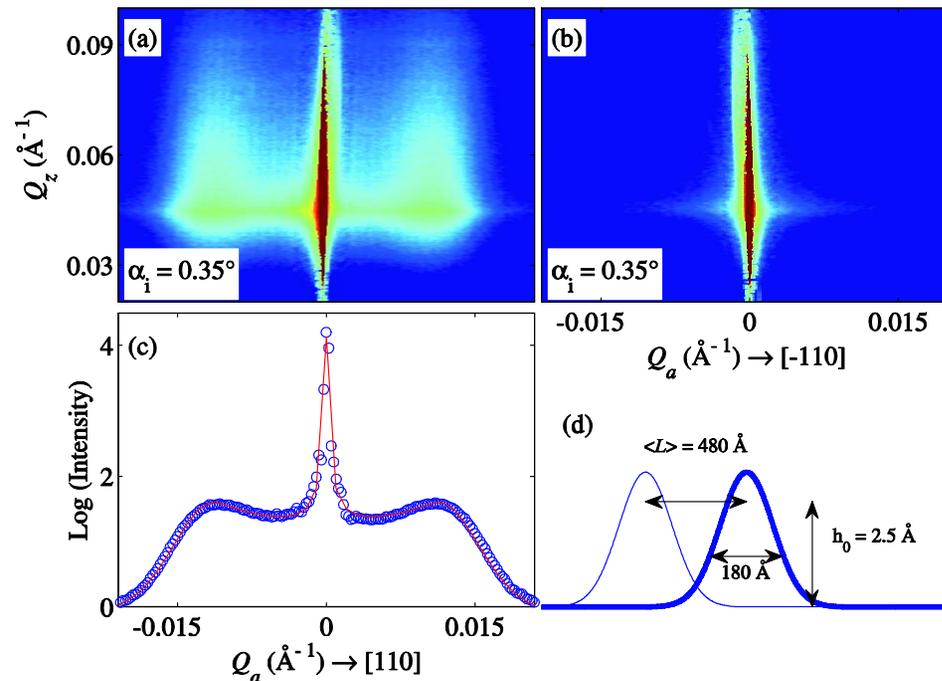
sample	t, Mn%	buffer	τ	RMS	K_u/K_c
Mn 352	5, 6%	A HT	49.7 ± 12.7	0.35 ± 0.07	0.241
Mn 536	5, 6%	B HT + B LT	45.5 ± 11.3	0.31 ± 0.04	0.157
Mn 396	7, 6%	B HT	47.7 ± 8.2	0.48 ± 0.06	0.498
Mn 381	7, 6%	B HT	41.9 ± 6.4	0.38 ± 0.04	0.325
Mn 555	7, 6%	A HT	47.7 ± 6.3	0.3 ± 0.1	0.158
Mn 535	7, 6%	B LT	45.4 ± 10.3	0.34 ± 0.04	0.089
Mn 394	7, 6%	A HT	59.8 ± 13.5	0.35 ± 0.05	0.249
Mn 437	25, 12%	A LT	51.5 ± 8.6	0.36 ± 0.06	0.113
Mn 438	25, 12%	A LT	61.7 ± 11.4	0.37 ± 0.07	0.149
Mn 554	25, 6%	B LT	56.0 ± 16.9	0.35 ± 0.04	0.039
Mn 499	25, 6%	A HT	47.8 ± 11.8	0.31 ± 0.05	0.018
Mn 330	25, 6%	A HT	65.9 ± 11.3	0.31 ± 0.09	0.107
Mn 490	25, 6%	A HT	52.5 ± 8.3	0.28 ± 0.03	-0.005

RMS vs magnetic anisotropy



- ✓ clear relation between the ratio of the magnetic anisotropy constants K_u/K_c and the **RMS** roughness
- ✓ the uniaxial anisotropy increases as the RMS roughness increases

GID experiment



- ✓ Scans with the primary beam directed across the ripples (a) show two symmetric satellites
- ✓ satellites are absent in the scans along the ripples (b)
- ✓ by fitting the profile in (a) by assuming Gaussian-shaped ripples we obtained a periodicity of about 48 nm

Conclusions

Our aim was to investigate the magnetic anisotropy in (Ga,Mn)As

- ▶ **AFM** and **X-ray GID** measurements have revealed the presence of **ripples** aligned along the $[1-10]$ direction on the surface of (Ga,Mn)As layers
- ▶ We find that the strength of the uniaxial anisotropy of these layers increases with the amplitude of the ripples.
- ▶ This suggests that **the symmetry breaking uniaxial anisotropy** observed in (Ga,Mn)As might be related to these symmetry breaking structural features
- ▶ **...more investigation...**
 - could give us the possibility to relate the formation of the periodic structures with the presence of uniaxial strain, that may lead to a deeper understanding of the origin of the magnetic anisotropy*

Thank you

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